

SPECIFICATION OF LED CHIP CN850-40S [INFRARED]

1) Commodity Type and Physical Characteristics.

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|----------------------|---------------------|------------------|------------|
| 1. Material | GaAlAs/GaAlAs (DDH) | | |
| 2. Electrode | Top Side | P (anode) side | : Au Alloy |
| | Bottom Side | N (cathode) side | : Au Alloy |
| 3. Electrode Pattern | Fig.1 | | |
| 4. Chip Size | Fig.2 | | |
| 5. Chip Thickness | Fig.2 | | |
| 6. Emission Area | Fig.2 | | |

2) Electro-Optical Characteristics

Parameters	Symbol	Condition	min.	typ.	max.	unit
Forward Voltage	V_f	$I_f=20\text{mA}$		1.3	1.5	V
Reverse Current	I_r	$V_r=5\text{V}$			10	μA
Power Intensity	P_o	$I_f=20\text{mA}$	3.0	5.0		mW
Peak Wavelength	λ_P	$I_f=20\text{mA}$	840	850	860	nm
Spectral Radiation Bandwidth	$\Delta\lambda$	$I_f=20\text{mA}$		40		nm
RiseTime	t_r	$I_f=20\text{mA}$		15		ns
FallTime	t_f	$I_f=20\text{mA}$		10		ns

‡ Die shall be mounted on TO-18 gold header without resin coated. ($T_a=25^\circ\text{C}$)

[Unit: μm]

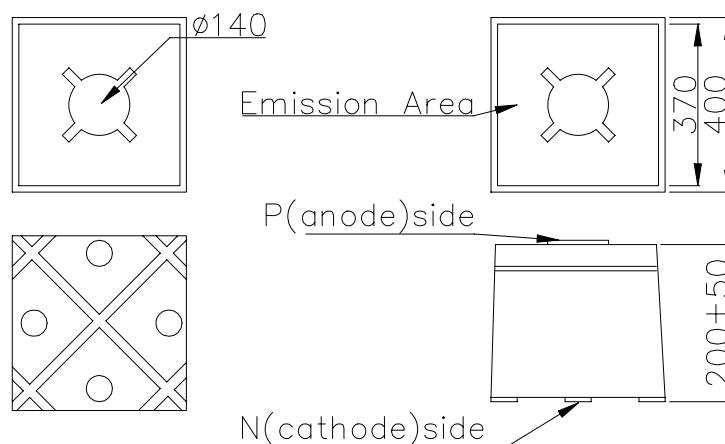


Fig.1 Electrode Pattern

Fig.2 Chip size and Emission Area